

CORRECTION

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Correction: The effect of device geometry and crystal orientation on the stress-dependent offset voltage of 3C–SiC(100) four terminal devices

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Correction for 'The effect of device geometry and crystal orientation on the stress-dependent offset voltage of 3C–SiC(100) four terminal devices' by Afzaal Qamar *et al.*, *J. Mater. Chem. C*, 2015, **3**, 8804–8809.

The details for ref. 34 are incorrect in the PDF version of this communication article. The correct details are given below¹ and were updated in the HTML version of the original article and republished on 26th August 2015.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

References

- 1 A. Qamar, H.-P. Phan, D. V. Dao, P. Tanner, T. Dinh, L. Wang and S. Dimitrijević, *IEEE Electron Device Lett.*, 2015, **36**(7), 708–710.

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